

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

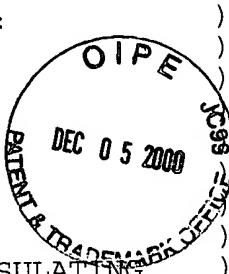
In re the Application of:

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING)
FILM FORMING METHOD,)
SEMICONDUCTOR DEVICE AND)
METHOD OF MANUFACTURING THE)
SAME)



Group Art Unit: 2814

Examiner: K. Eaton

ATTENTION AU 2814
EXPEDITED PROCESSING
RESPONSE TO FINAL ACTION

2018 (NY)
12/13/00
CABRAN

A. J. Russell
1-12-01

RESPONSE TO FINAL ACTION OF JULY 5, 2000

Assistant Commissioner for Patents
Washington, D.C. 20231

RECEIVED

DEC 12 2000

TECHNOLOGY CENTER 2800

Sir:

Responsive to the "final" rejection of July 5, 2000, please
amend the captioned application as follows:

IN THE CLAIMS:

Please cancel all pending claims and substitute therefor the
following new claims 43-52:

43. A stress-adjusted insulating film forming method for forming
a multilayered insulating film on a substrate, said method
comprising:

(a) forming a first insulating layer with a first type of
stress;

(b) forming a conductive interconnection layer on and in